



UF3055

Power MOSFET

N-CHANNEL ENHANCEMENT MODE POWER MOSFET

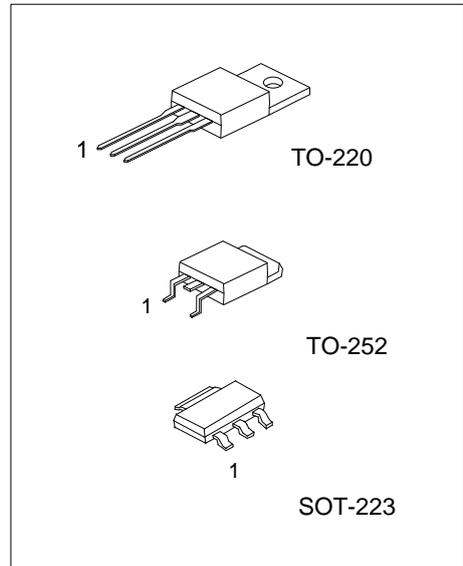
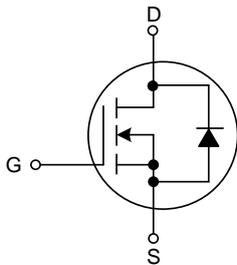
DESCRIPTION

As an N-channel enhancement mode power MOSFET, the UTC UF3055 is designed for low voltage, high speed switching applications in power supplies, converters and power motor controls and bridge circuits.

FEATURES

* $R_{DS(ON)} \leq 110 \text{ m}\Omega @ V_{GS} = 10 \text{ V}, I_D = 1.5 \text{ A}$

SYMBOL



ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UF3055L-AA3-R	UF3055G-AA3-R	SOT-223	G	D	S	Tape Reel
UF3055L-TA3-R	UF3055G-TA3-R	TO-220	G	D	S	Tube
UF3055L-TN3-R	UF3055G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>UF3055G-AA3-R</p> <p>(1) Packing Type</p> <p>(2) Package Type</p> <p>(3) Green Package</p>	<p>(1) R: Tape Reel, T: Tube</p> <p>(2) AA3: SOT-223, TA3: TO-220, TN3: TO-252</p> <p>(3) G: Halogen Free and Lead Free, L: Lead Free</p>
---	---

MARKING

SOT-223	TO-220 / TO-252
<p>UF3055 □ □□□□ □ 1</p> <p>L: Lead Free G: Halogen Free Date Code</p>	<p>UTC UF3055 □ □□□□ □ 1</p> <p>Lot Code ← L: Lead Free G: Halogen Free Date Code</p>

■ **ABSOLUTE MAXIMUM RATINGS** ($T_C = 25^\circ\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain Source Voltage	V_{DSS}	60	V
Drain Gate Voltage ($R_{GS} = 10M\Omega$)	V_{DGR}	60	V
Gate Source Voltage	V_{GSS}	Continuous	± 20
		Non-Repetitive ($t_P \leq 10 \text{ ms}$)	± 30
Continuous Drain Current ($T_A = 25^\circ\text{C}$)	I_D	3.0	A
Pulsed Drain Current ($t_P \leq 10 \mu\text{s}$)	I_{DM}	9.0	A
Single Pulsed Avalanche Energy (Note 2)	EAS	74	mJ
Power Dissipation ($T_A = 25^\circ\text{C}$)	SOT-223	0.8	W
	TO-220	2	W
	TO-252	1.13	W
Junction Temperature	T_J	+150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 ~ +175	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. $T_J = 25^\circ\text{C}$, $V_{DD} = 25\text{V}$, $V_{GS} = 10\text{V}$, $I_L = 7.0\text{A}$, $L = 3.0\text{mH}$, $V_{DS} = 60\text{V}$

■ **THERMAL DATA**

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient (Note)	θ_{JA}	SOT-223	150
		TO-220	62
		TO-252	110

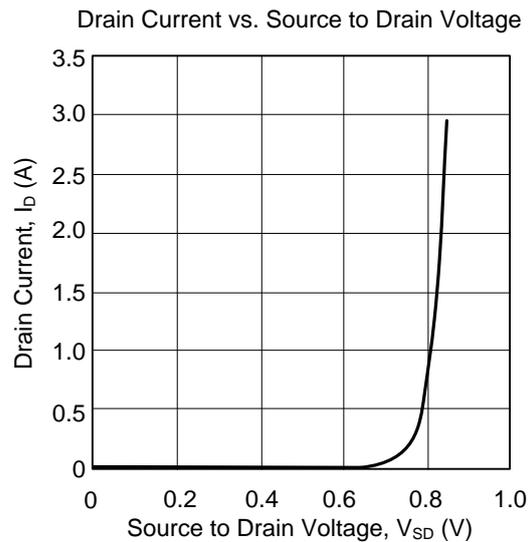
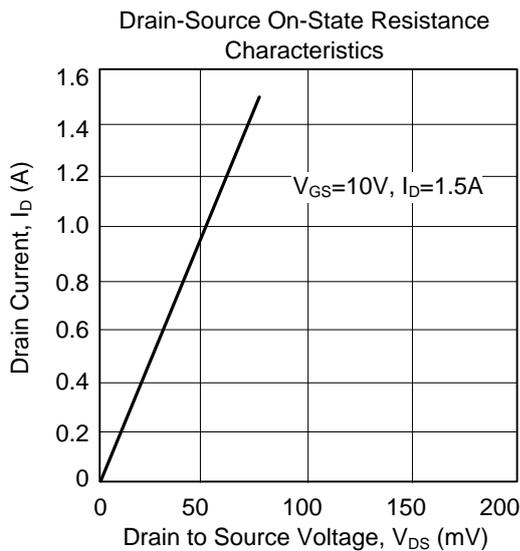
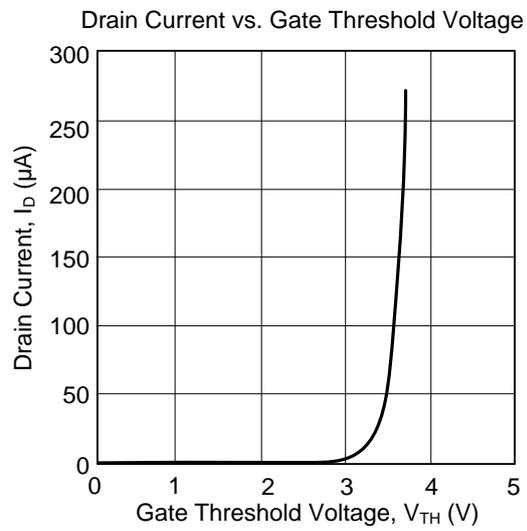
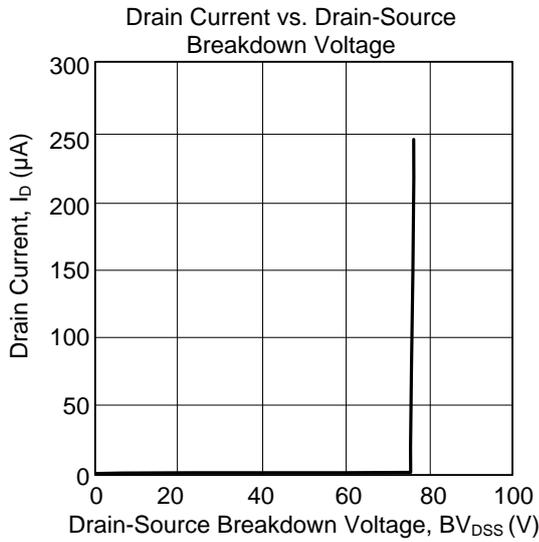
■ ELECTRICAL CHARACTERISTICS (T_J =25°C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain Source Breakdown Voltage (Note 1)	BV _{DSS}	V _{GS} = 0V, I _D =250μA	60	68		V
Temperature Coefficient (Positive)				66		mV/°C
Drain-Source Leakage Current	I _{DSS}	V _{GS} =0V, V _{DS} =60V			1.0	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = ±20 V, V _{DS} =0V			±100	nA
ON CHARACTERISTICS (Note 1)						
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} , I _D =250μA	2.0	3.0	4.0	V
Temperature Coefficient (Negative)					6.6	
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10 V, I _D =1.5A		50	110	mΩ
Static Drain-to-Source On-Resistance	V _{DS(ON)}	V _{GS} =10 V, I _D =3A		0.15	0.40	V
Forward Transconductance	g _{FS}	V _{DS} =8.0V, I _D =1.7A		3.2		S
DYNAMIC PARAMETERS						
Input Capacitance	C _{ISS}	V _{GS} =0 V, V _{DS} =25 V, f=1.0MHz		700	780	pF
Output Capacitance	C _{OSS}			180	210	pF
Reverse Transfer Capacitance	C _{RSS}			20	50	pF
SWITCHING PARAMETERS (Note 2)						
Total Gate Charge	Q _G	V _{GS} =10V, V _{DS} =48V, I _D =3.0A (Note 1)		50	70	nC
Gate-Source Charge	Q _{GS}			6		nC
Gate-Drain Charge	Q _{GD}			3		nC
Turn-ON Delay Time	t _{D(ON)}	V _{GS} =10V, V _{DD} =30V, I _D =3.0A , R _G =9.1Ω (Note 1)		50	70	ns
Turn-ON Rise Time	t _R			40	60	ns
Turn-OFF Delay Time	t _{D(OFF)}			95	115	ns
Turn-OFF Fall-Time	t _F			30	50	ns
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =3.0A		0.89	1.0	V
Body Diode Reverse Recovery Time	t _{rr}	V _{GS} =0V, I _S =3.0A, dI/dt=100 A/μs (Note 1)		30		ns
	t _A			22		ns
	t _B			8.6		ns
Body Diode Reverse Recovery Charge	Q _{rr}			0.04		nC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.

2. Switching characteristics are independent of operating junction temperatures.

■ TYPICAL CHARACTERISTICS



UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. UTC reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.